EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	18	("20020044111"|"20020056838"|" 20020074547"|"20020100908"|"2 0020179906"|"20030054653"|"20 030134519"|"20030232128"|"200 40147113"|"5162901"|"5640067"| "5897328"|"5989945"|"6291136"| "6593591"|"6849308"|"6853083"| "6992435").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/12/04 10:01
S2	18	("20020044111"|"20020056838"|" 20020074547"|"20020100908"|"2 0020179906"|"20030054653"|"20 030134519"|"20030232128"|"200 40147113"|"5162901"|"5640067"| "5897328"|"5989945"|"6291136"| "6593591"|"6849308"|"6853083"| "6992435").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2007/12/04 10:01
S3	18	S1 and S2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2007/12/04 10:01
S4	15208	form$3 near3 (first electrode) same substrate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 10:11
S5	664	form$3 near3 (first insulat$3 film) same first electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 10:14
S6	408	S4 and S5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 10:12

EAST Search History

S7	373	form$3 near3 (first semiconductor layer or first layer) same (first insulat$3 film)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 10:13
S8	335	form$3 near3 (second insulat$3 film) same (first semiconductor layer or first layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 10:15
S9	194	S7 and S8	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 10:15
S10	21	S6 and S9	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 10:35
S11	14	("20020117691"|"20030107037"|"20040207792"|"20050213013"|"5598285"|"5838037"|"5946060"|"5990987"|"6028653"|"6097454"|"6266166"|"6288763"|"6297866"|"6356318").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; IBM_TDB	OR	ON	2007/12/04 10:34
S12	14	S11 and (form$3 or first or second or third or fourth or electrode or layer or insulat$3 or film or contact or cover or semiconductor or substrate or pattern$3 or mask or overlap or electrical or connect$3 or droplet or discharge or n-type or p-type or n type or p type or hydrophilic or liquid -repellent or liquid repellent or plasma treatment or photocatalytic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 10:42

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S13	18	S3 and (form$3 or first or second or third or fourth or electrode or layer or insulat$3 or film or contact or cover or semiconductor or substrate or pattern$3 or mask or overlap or electrical or connect$3 or droplet or discharge or n-type or p-type or n type or p type or hydrophilic or liquid -repellent or liquid repellent or plasma treatment or photocatalytic)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 10:41
S14	0	S12 and S13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 10:43
S15	32	S12 or S13	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/06 19:17
S16	201681	plural$3 near3 layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:25
S17	38243	(insulat$3 near3 layer and semiconductor layer and electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:27
S18	8625	S16 and S17	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:27

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S19	45143	(first and second and third and fourth) near5 layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:32
S20	1724	S18 and S19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:28
S21	23924	(first and second and third and fourth) near5 electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:33
S22	10345	(first and second and third and fourth)adj3 electrode	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:34
S23	10345	S21 and S22	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:33
S24	171	S20 and S23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:33
S25	2672	(first and second and third and fourth)adj3 insulat$3 film	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:34

S26	43	S24 and S25	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:35
S27	5891	semiconductor energy laboratory . as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:36
S28	34	S26 NOT S27	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/04 11:36
S29	1	base near$3 treatment	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/06 19:18
S30	1	droplet near$3 discharge	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/06 19:20
S31	3	drop near$3 discharge	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/06 19:21
S32	2	("4628331").PN. OR ("6089694"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/12/06 19:23
S33	19	("1637386" | "2054438" | "2295710" | "3513092" | "3864263" | "4534211" | "5200248" | "5491642" | "H000337").PN. OR ("5792941"). URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/12/06 20:02

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S34	838	electrode with droplet with discharge	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/12/06 20:03
S35	146	S34 and ("257" or "438").clas.	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/12/06 20:03
S36	111	S35 and (LCD or "liquid crystal")	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/12/06 20:05
S37	5914	semiconductor energy laboratory . as.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/12/06 20:05
S38	51	S36 NOT S37	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/12/06 20:07